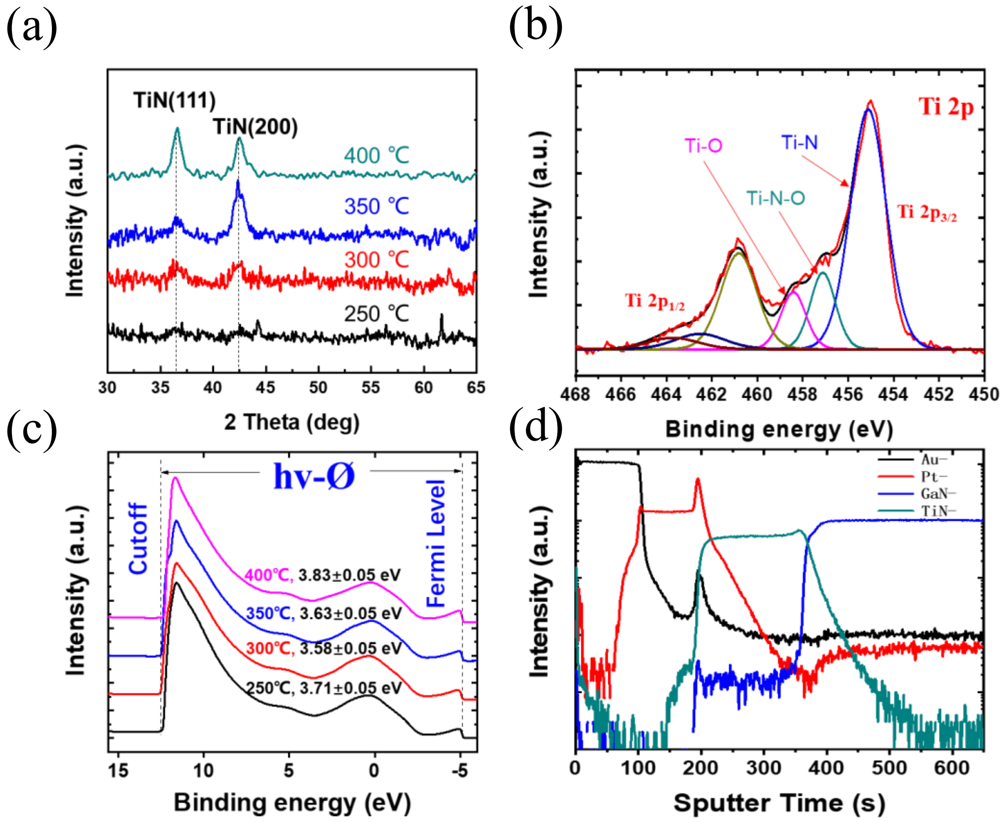

Figure. (a) XRD patterns TiN films deposited at different temperatures; (b) High resolution XPS spectra of Ti 2p orbital in TiN films deposited at 350 ℃. Binding energy was calibrated with C-C peaks; (c) UPS measurement of TiN films deposited at different temperatures with -5 bias voltage applied on the sample; (d) *n*-GaN/TiN(50nm)/Pt(50nm)/Au(100nm) sample annealed at 700 ℃ in N_2 for 1 min ToF-SIMS depth profile.